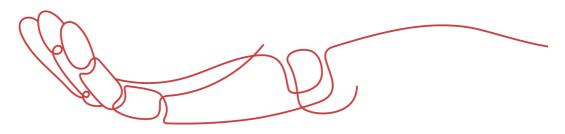


PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at



Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

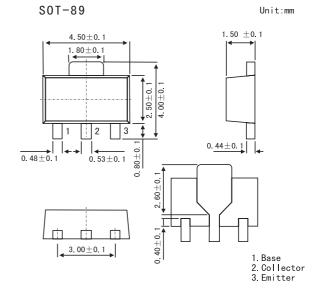


FCX690BTA

NPN Silicon Power Switching Transistor

Features

- 2W power dissipation.
- 6A peak pulse current.
- Gain of 400 @lc=1Amp.
- Very low saturation voltage.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	Vсво	45	V
Collector-emitter voltage	Vceo	45	V
Emitter-base voltage	Vebo	5	V
Continuous collector current	Ісм	6	А
Peak pulse current	lc	2	А
Power dissipation	Ptot	1	W
Operating and storage temperature range	Tj,Tstg	-55 to +150	°C





Electrical Characteristics Ta = 25 $^{\circ}$ C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	Ic=100µA	45			V
Collector-emitter breakdown voltage *	V(BR)CEO	Ic=10mA	45			V
Emitter-base breakdown voltage	V(BR)EBO	Iε=100μA	5			V
Collector Cut-Off Current	Ісво	Vcb=9V			0.1	μA
Emitter Cut-Off Current	Іево	VEB=4V			0.1	μA
Collector-emitter saturation voltage *	VCE(sat)	Ic=0.1A, Iв=0.5mA Ic=1A, Iв=5mA			80 300	mV
Base-emitter saturation voltage *	VBE(sat)	Ic=1А, Iв=10mА			1.1	V
Base-emitter ON voltage *	VBE(on)	IC=1A, VCE=2V			1.0	V
Static Forward Current Transfer Ratio*	hfe	Ic=100mA,Vce=2V Ic=1A,Vce=2V Ic=2A,Vce=2V	500 400 150			
Transitional frequency	fτ	Ic=50mA, Vce=5V, f=50MHz	150			MHz
Input capacitance	Cibo	Veb=0.5V, f=1MHz		200		pF
Output capacitance	Cobo	Vсв=10V, f=1MHz		16		pF
Turn-on time	t(on)	Ic=500mA, Vcc=10V		33		ns
Turn-off time	t(off)	Ів1=Ів2=50mA		1300		ns

* Pulse test: tp = 300 μ s; d \leq 0.02.





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